Sergei I Kozlovskiy

List of Publications by Year
in descending order

13 papers	**63** citations	1937685 **4** h-index	1588992 **8** g-index
13 all docs	**13** docs citations	**13** times ranked	**42** citing authors

#	Article	IF	Citations
1	First-order piezoresistance coefficients in heavily doped p-type silicon crystals. Sensors and Actuators A: Physical, 2007, 133, 72-81.	4.1	15
2	Investigation of conductivity and piezoresistance of n-type silicon on basis of quantum kinetic equation and model distribution function. Sensors and Actuators A: Physical, 2008, 147, 17-33.	4.1	14
3	Piezoresistive effect in p-type silicon classical nanowires at high uniaxial strains. Journal of Computational Electronics, 2011, 10, 258-267.	2.5	10
4	Piezoresistance effect in n-type silicon: from bulk to nanowires. Journal of Computational Electronics, 2014, 13, 515-528.	2.5	4
5	Dilatation deformation potential, drift mobility and piezoresistance in p-type silicon (quantum kinetic) Tj ETQq1 1 0.784314 rgBT /Overl	2.5	4
6	Ionized impurity scattering in quantum wells and quantum wires. Journal of Applied Physics, 2020, 128, 174301.	2.5	4
7	A silicon stress-sensitive unijunction transistor. Technical Physics, 2002, 47, 438-443.	0.7	3
8	Strain induced mobility enhancement in p-type silicon structures: Bulk and quantum well (quantum) Tj ETQq0 0 0 rgBT /Overlock 10 Tf 5	2.5	3
9	A quantum kinetic approach for calculating low-field mobility in black phosphorus crystals and multilayer phosphorene. Journal of Computational Electronics, 2018, 17, 1549-1556.	2.5	2
10	Electron Mobility in Molybdenum Disulfide: From Bulk to Monolayer. Physica Status Solidi (B): Basic Research, 2020, 257, 1900635.	1.5	2
11	Quantum kinetics approach to calculation of the low field mobility in the hole inversion layers of silicon MOSFETâ€™s. Journal of Computational Electronics, 2018, 17, 926-933.	2.5	1
12	Multi-ion scattering of charged carriers by ionized impurities in heavily doped semiconductors: From bulk to nanowires. Journal of Applied Physics, 2022, 131, 125708.	2.5	1
13	Longitudinal piezoresistance and conductance of the p-type silicon nanostructures in ballistic transport regime: from bulk to nanowires. Journal of Computational Electronics, 2012, 11, 203-215.	2.5	0